

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1150	(438/710).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/01/21 13:53
L2	267	(156/345.31).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/01/21 13:56
L3	221	muraoka-yusuke\$.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 13:57
L4	57	saito-kimitsugu\$.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 13:58
L5	11	fukatsu-eiji\$.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 13:58
L6	10	sarumaru-shogo\$.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 13:59
L7	28	oshiba-hisanori\$.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 13:59
L8	627	watanabe-katsumi\$.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 14:00

L9	6	munemasa-jun\$. <i>in</i> .	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 14:00
L10	2	gama-takashi\$. <i>in</i> .	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 14:01
L11	178	okuyama-yasuo\$. <i>in</i> .	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 14:01
L12	2493	(118/50).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/01/21 14:14
L13	954	(118/320).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/01/21 14:14

L9	6	munemasa-jun\$.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 14:00
L10	2	gama-takashi\$.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 14:01
L11	178	okuyama-yasuo\$.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 14:01
S2	176	(yewebdar or tadesse) and ("118"/\$.ccls. or "264"/\$.ccls.)	US-PGPUB; USPAT	OR	OFF	2005/01/19 16:28
S77	1	10/700020	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/11 11:31
S78	5	(("5700379") or ("6358673") or ("6554507")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/01/11 11:35
S79	0	anti near dry\$3 near5 solution and S78	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/11 11:45
S80	0	2002/0132192	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/11 11:36
S81	2	"20020132192"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/11 11:37

S82	2	"20020160625"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/11 11:37
S83	1423	(118/52).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/01/11 11:42
S84	390	(118/612).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/01/11 11:42
S85	0	anti near dry\$3 near5 solution and S83	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/11 11:43
S86	1	anti near dry\$3 and S83	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/11 11:44
S87	1	anti near dry\$3 near5 solution and spin near coating	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/11 11:45
S88	6	anti near dry\$3 and spin near coating	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/11 12:00
S89	12	anti near dry\$3 near agent\$1 and wafer\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/11 11:47
S90	696	air near dry and spin near coating	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/11 12:00

S91	45	SCF and spin near coating	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/11 12:01
S92	3942	surfactant and spin near coating	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/11 12:02
S93	7	surfactant and spin near coating and 118/52.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/11 12:05
S94	5	fluorocarbon\$5 and spin near coating and 118/52.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/11 12:07
S95	8	fluorocarbon\$5 and 118/52.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/11 12:07
S97	4	(("5200017") or ("6269552")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/01/13 10:20
S99	2	10/132212	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/13 11:08
S100	13	("4347302"   "4778532"   "4917123"   "5200017"   "5306350"   "5700379"   "5873177"   "6001191"   "6067727"   "6110011"   "6235122"   "6269552"   "6352467").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/13 11:09
S101	0	S100 and affinity	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/13 11:09
S102	2	anti near dry\$3 same affinity	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/13 11:10

S10 3	38	supercritical near fluid same affinity	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/13 11:12
S10 4	9	S103 and (semiconductor\$1 or wafer\$1)	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/13 11:59
S10 6	1	10/066823	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/13 11:59
S10 7	19	("5200017").URPN.	USPAT	OR	OFF	2005/01/19 08:06
S10 8	4	S107 and wet same process\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/18 13:45
S10 9	185	438/7\$.ccls. and wet near process\$3 near7 dry\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/18 13:50
S11 0	6	438/7\$.ccls. and wet near process\$3 same prevent\$3 near5 dry\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/18 13:34
S11 1	3	S107 and wet same process\$3 same supply\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/18 13:45
S11 2	10	438/7\$.ccls. and wet near process\$3 near7 supply\$3 near7 (solution or liquid)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/18 14:06
S11 3	1	09/891829	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/18 13:52

S11 5	3	438/7\$.ccls. and nozzles near3 supply\$3 near5 (develop\$3 or rins\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/18 16:19
S11 6	7	spin near coat\$3 and nozzles near3 supply\$3 near5 (develop\$3 same rins\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/18 14:20
S11 7	11	("4021278"   "4373991"   "4544446"   "4618564"   "5208133"   "5213946"   "5885745"   "5998092"   "6190063"   "6241403"   "6458607").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/18 14:16
S11 8	0	spin near coat\$3 and nozzles same supply\$3 near5 (develop\$3 same rins\$3 same deionized near water)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/18 14:21
S11 9	53	spin near coat\$3 and nozzles same supply\$3 near5 (develop\$3 or rins\$3 or (deionized near water))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/18 14:39
S12 0	1	spin near coat\$3 and nozzles same supply\$3 near5 (rins\$3 near5(deionized near water))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/18 14:40
S12 1	380	high near pressure same develop\$3 same wafer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/18 16:22
S12 2	14	438/7\$.ccls. and S121	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/18 16:19
S12 3	48	high near pressure near7 develop\$3 near3 (wafer or substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/18 16:32

S12 4	20	high near pressure near7 developed near3 (wafer or substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/18 16:46
S12 5	33	high near pressure near10 developed near3 (wafer or substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/18 16:47
S12 6	13	S125 not S124	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/18 16:47
S12 7	0	("6703316").URPN.	USPAT	OR	OFF	2005/01/18 17:19
S12 8	2	wet near transport\$3 near5 (wafer or substrate) and "438"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/18 17:22
S12 9	4	wet near transport\$3 near5 (wafer or substrate) and "118"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/18 17:22
S13 0	19	("5200017").URPN.	USPAT	OR	OFF	2005/01/19 08:12
S13 1	13	affinity near10 high near pressure near fluid	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/19 16:30
S13 2	50	scf same high\$2 near affinity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/19 16:33
S13 3	12	scf near10 high\$2 near affinity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/19 16:34

S13 4	13	("4347302"   "4778532"   "4917123"   "5200017"   "5306350"   "5700379"   "5873177"   "6001191"   "6067727"   "6110011"   "6235122"   "6269552"   "6352467").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/21 10:18
S13 5	3	S134 and pressure near vessel\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 10:29
S13 6	11	"134"/\$.ccls. and pressure near vessels and wafer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 10:24
S13 7	9	plurality near7 pressure near vessels and wafer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 10:37
S13 8	2275	(134/902).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/01/21 10:29
S13 9	6	S138 and pressure near vessels	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 10:30
S14 0	32	S138 and high near pressure same supercritical	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 10:31
S14 1	22	high near pressure near vessels and wafer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 10:42
S14 2	6	high near pressure near (vessels or units or chambers) and wafer and "427"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 10:43

S14 3	3	high near pressure near (vessels or units or chambers) and wafer and "118"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 10:43
----------	---	-------------------------------------------------------------------------------------	-------------------------------------------------------------------	----	-----	------------------